

MAC15 Series

Triacs

Silicon Bidirectional Thyristors

Designed primarily for full-wave ac control applications, such as solid-state relays, motor controls, heating controls and power supplies; or wherever full-wave silicon gate controlled solid-state devices are needed. Triac type thyristors switch from a blocking to a conducting state for either polarity of applied main terminal voltage with positive or negative gate triggering.

Features

- Blocking Voltage to 800 V
- All Diffused and Glass Passivated Junctions for Greater Parameter Uniformity and Stability
- Small, Rugged, Thermowatt Construction for Low Thermal Resistance, High Heat Dissipation and Durability
- Gate Triggering Guaranteed in Three Modes (MAC15 Series) or Four Modes (MAC15A Series)
- These Devices are Pb-Free and are RoHS Compliant*

MAXIMUM RATINGS ($T_J = 25^\circ\text{C}$ unless otherwise noted)

Rating	Symbol	Value	Unit
Peak Repetitive Off-State Voltage Note 1 ($T_J = -40$ to $+125^\circ\text{C}$, Sine Wave 50 to 60 Hz, Gate Open) MAC15A6G MAC15-8G, MAC15A8G MAC15-10G, MAC15A10G	V_{DRM} , V_{RRM}	400 600 800	V
Peak Gate Voltage (Pulse Width ≤ 1.0 μsec ; $T_C = 90^\circ\text{C}$)	V_{GM}	10	V
On-State Current RMS; Full Cycle Sine Wave 50 to 60 Hz ($T_C = +90^\circ\text{C}$)	$I_{\text{T(RMS)}}$	15	A
Circuit Fusing Consideration ($t = 8.3$ ms)	I^2t	93	A^2s
Peak Non-Repetitive Surge Current (One Full Cycle Sine Wave, 60 Hz, $T_C = +80^\circ\text{C}$) Preceded and Followed by Rated Current	I_{TSM}	150	A
Peak Gate Power ($T_C = +80^\circ\text{C}$, Pulse Width = 1.0 μs)	P_{GM}	20	W
Average Gate Power ($T_C = +80^\circ\text{C}$, $t = 8.3$ ms)	$P_{\text{G(AV)}}$	0.5	W
Peak Gate Current (Pulse Width ≤ 1.0 μsec ; $T_C = 90^\circ\text{C}$)	I_{GM}	2.0	A
Operating Junction Temperature Range	T_J	-40 to $+125$	$^\circ\text{C}$
Storage Temperature Range	T_{stg}	-40 to $+150$	$^\circ\text{C}$

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

1. V_{DRM} and V_{RRM} for all types can be applied on a continuous basis. Blocking voltages shall not be tested with a constant current source such that the voltage ratings of the devices are exceeded.

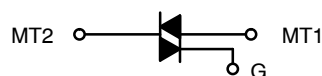
*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.



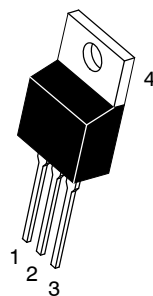
ON Semiconductor®

<http://onsemi.com>

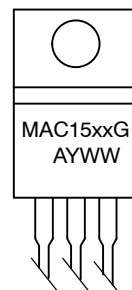
TRIACS 15 AMPERES RMS 400 thru 800 VOLTS



MARKING DIAGRAM



TO-220AB
CASE 221A
STYLE 4



MAC15xx = Specific Device Code
xx = See Table on Page 2
A = Assembly Location (Optional)*
Y = Year
WW = Work Week
G = Pb-Free Package

* The Assembly Location code (A) is optional. In cases where the Assembly Location is stamped on the package the assembly code may be blank.

PIN ASSIGNMENT

	PIN ASSIGNMENT
1	Main Terminal 1
2	Main Terminal 2
3	Gate
4	Main Terminal 2

ORDERING INFORMATION

See detailed ordering, marking, and shipping information in the package dimensions section on page 2 of this data sheet.

MAC15 Series

THERMAL CHARACTERISTICS

Characteristic	Symbol	Value	Unit
Thermal Resistance, Junction-to-Case	$R_{\theta JC}$	2.0	$^{\circ}\text{C}/\text{W}$
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	62.5	$^{\circ}\text{C}/\text{W}$
Maximum Lead Temperature for Soldering Purposes 1/8" from Case for 10 Seconds	T_L	260	$^{\circ}\text{C}$

ELECTRICAL CHARACTERISTICS ($T_C = 25^{\circ}\text{C}$ unless otherwise noted; Electricals apply in both directions)

Characteristic	Symbol	Min	Typ	Max	Unit
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OFF CHARACTERISTICS

Peak Blocking Current ($V_D = \text{Rated } V_{DRM}, V_{RRM}$; Gate Open)	I_{DRM}, I_{RRM}	$T_J = 25^{\circ}\text{C}$	–	–	10	μA
		$T_J = 125^{\circ}\text{C}$	–	–	2.0	mA

ON CHARACTERISTICS

Peak On-State Voltage Note 2 ($I_{TM} = \pm 21 \text{ A Peak}$)	V_{TM}	–	1.3	1.6	V
Gate Trigger Current (Continuous dc) ($V_D = 12 \text{ Vdc}, R_L = 100 \Omega$) MT2(+), G(+) MT2(+), G(–) MT2(–), G(–) MT2(–), G(+) "A" SUFFIX ONLY	I_{GT}	–	–	50	mA
		–	–	50	
		–	–	50	
		–	–	75	
		–	–	75	
Gate Trigger Voltage (Continuous dc) ($V_D = 12 \text{ Vdc}, R_L = 100 \Omega$) MT2(+), G(+) MT2(+), G(–) MT2(–), G(–) MT2(–), G(+) "A" SUFFIX ONLY	V_{GT}	–	0.9	2	V
		–	0.9	2	
		–	1.1	2	
		–	1.4	2.5	
		–	1.4	2.5	
Gate Non-Trigger Voltage ($V_D = 12 \text{ V}, R_L = 100 \Omega, T_J = 110^{\circ}\text{C}$) MT2(+), G(+); MT2(–), G(–); MT2(+), G(–) MT2(–), G(+) "A" SUFFIX ONLY	V_{GD}	0.2	–	–	V
		0.2	–	–	
Holding Current ($V_D = 12 \text{ Vdc}$, Gate Open, Initiating Current = $\pm 200 \text{ mA}$)	I_H	–	6.0	40	mA
Turn-On Time ($V_D = \text{Rated } V_{DRM}, I_{TM} = 17 \text{ A}$) ($I_{GT} = 120 \text{ mA}$, Rise Time = $0.1 \mu\text{s}$, Pulse Width = $2 \mu\text{s}$)	t_{gt}	–	1.5	–	μs

DYNAMIC CHARACTERISTICS

Critical Rate of Rise of Commutation Voltage ($V_D = \text{Rated } V_{DRM}, I_{TM} = 21 \text{ A}$, Commutating $di/dt = 7.6 \text{ A/ms}$, Gate Unenergized, $T_C = 80^{\circ}\text{C}$)	$dv/dt(c)$	–	5.0	–	$\text{V}/\mu\text{s}$
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2. Pulse Test: Pulse Width $\leq 2.0 \text{ ms}$, Duty Cycle $\leq 2\%$.

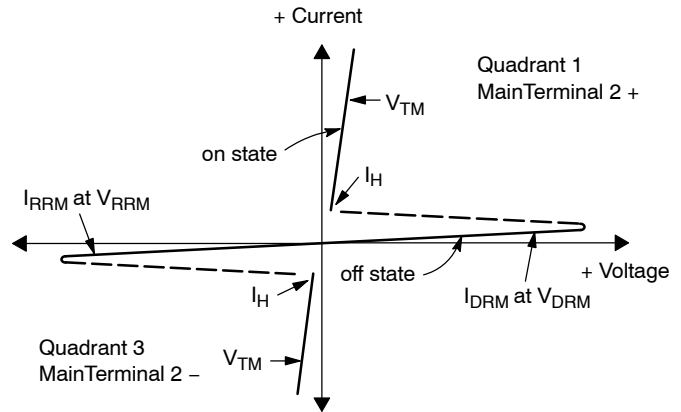
ORDERING INFORMATION

Device	Device Marking	Package	Shipping
MAC15-8G	MAC15-8	TO-220AB (Pb-Free)	500 Units Bulk
MAC15-10G	MAC1510	TO-220AB (Pb-Free)	
MAC15A6G	MAC15A6	TO-220AB (Pb-Free)	
MAC15A8G	MAC15A8	TO-220AB (Pb-Free)	
MAC15A10G	MAC15A10	TO-220AB (Pb-Free)	

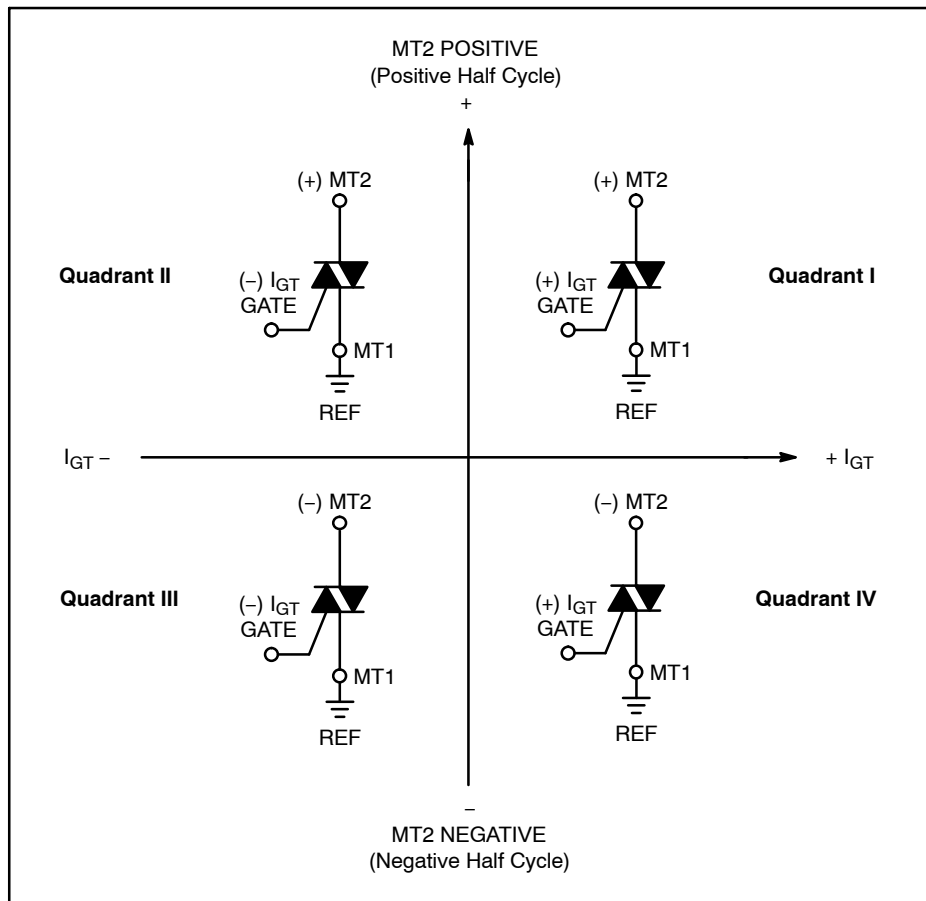
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Voltage Current Characteristic of Triacs (Bidirectional Device)

Symbol	Parameter
V_{DRM}	Peak Repetitive Forward Off State Voltage
I_{DRM}	Peak Forward Blocking Current
V_{RRM}	Peak Repetitive Reverse Off State Voltage
I_{RRM}	Peak Reverse Blocking Current
V_{TM}	Maximum On State Voltage
I_H	Holding Current



Quadrant Definitions for a Triac



All polarities are referenced to MT1.

With in-phase signals (using standard AC lines) quadrants I and III are used.

MAC15 Series

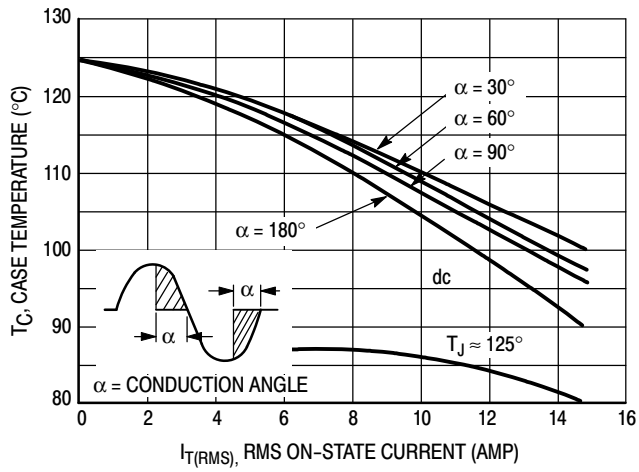


Figure 1. RMS Current Derating

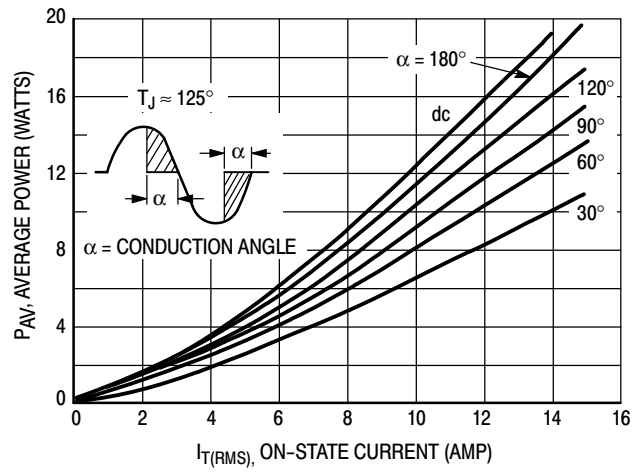


Figure 2. On-State Power Dissipation

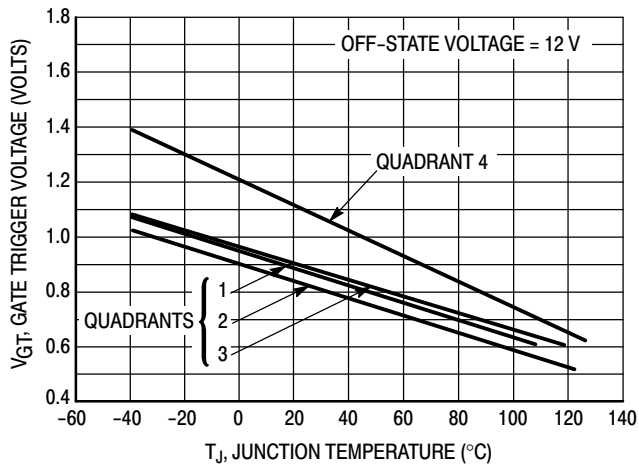


Figure 3. Typical Gate Trigger Voltage

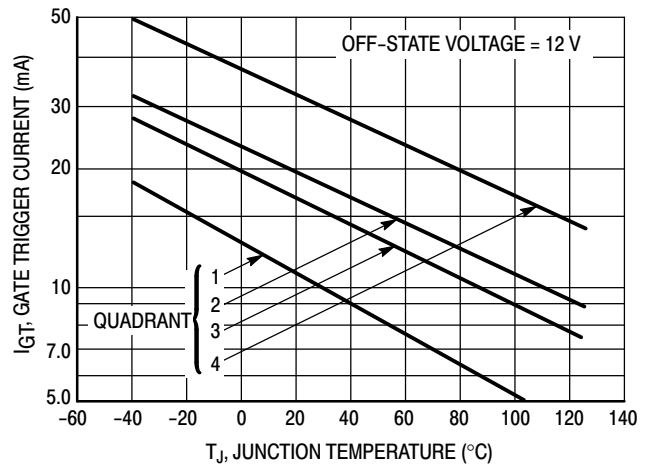
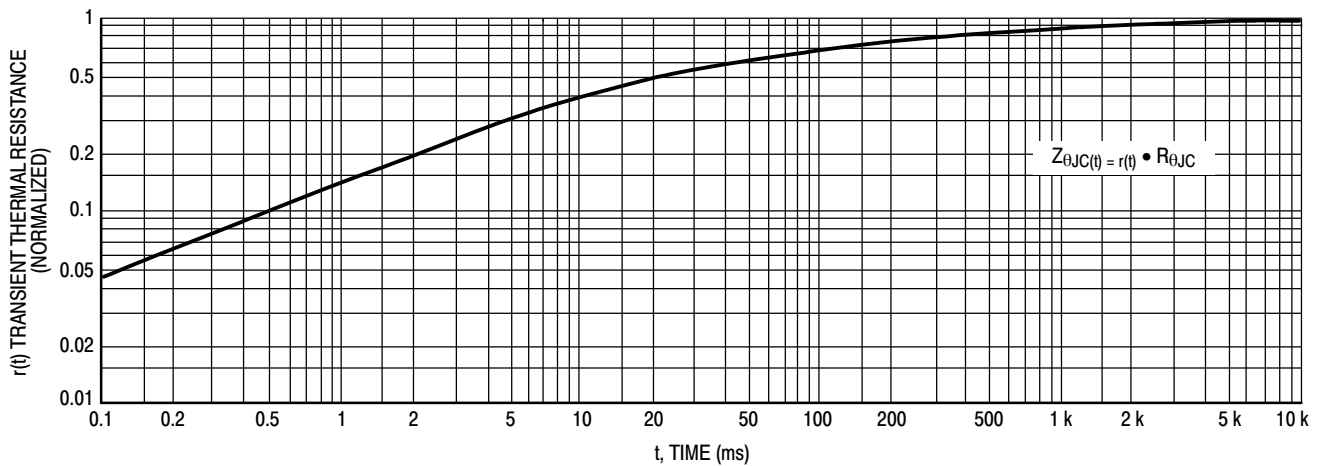
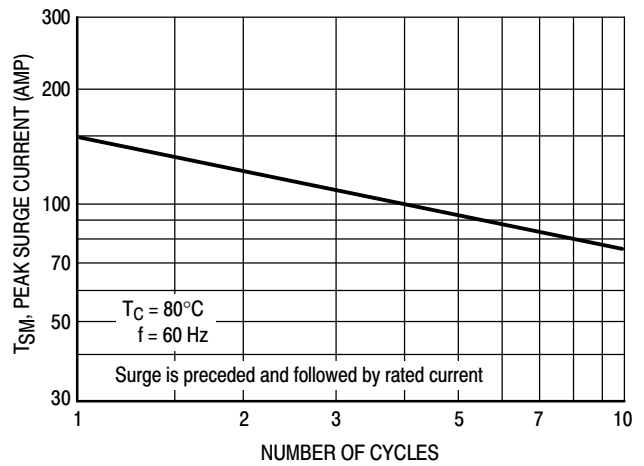
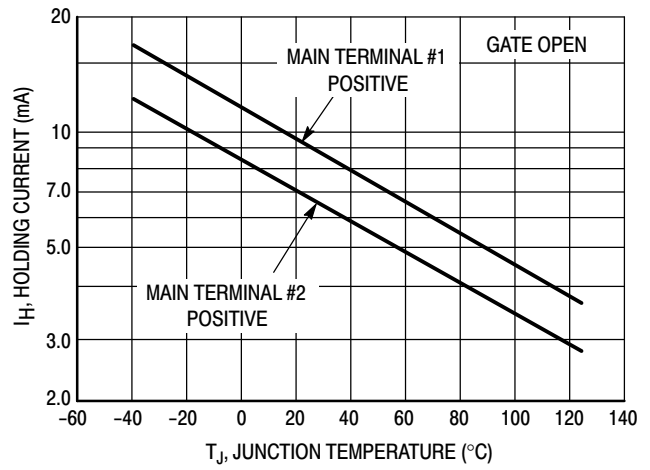
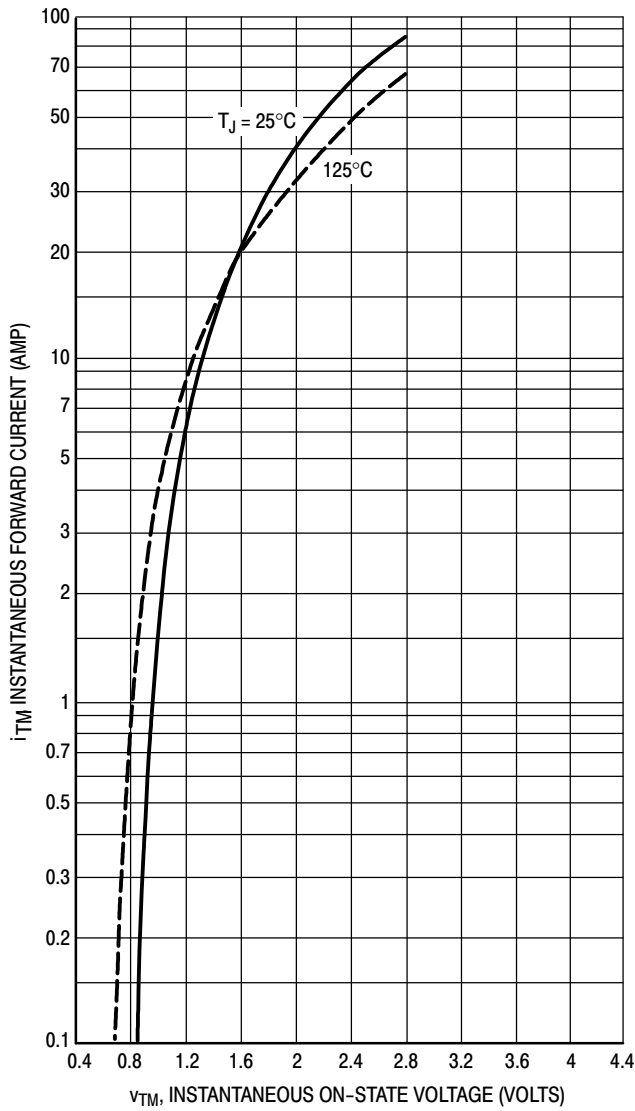


Figure 4. Typical Gate Trigger Current

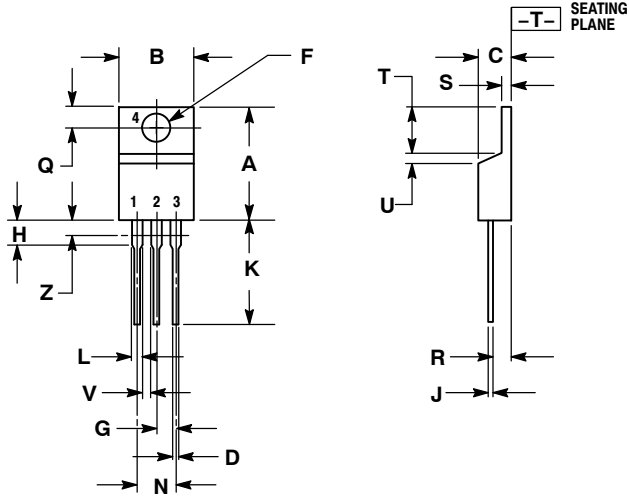
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PACKAGE DIMENSIONS

TO-220
CASE 221A-09
ISSUE AG



NOTES:

1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH.
3. DIMENSION Z DEFINES A ZONE WHERE ALL BODY AND LEAD IRREGULARITIES ARE ALLOWED.

DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.570	0.620	14.48	15.75
B	0.380	0.405	9.66	10.28
C	0.160	0.190	4.07	4.82
D	0.025	0.036	0.64	0.91
F	0.142	0.161	3.61	4.09
G	0.095	0.105	2.42	2.66
H	0.110	0.161	2.80	4.10
J	0.014	0.025	0.36	0.64
K	0.500	0.562	12.70	14.27
L	0.045	0.060	1.15	1.52
N	0.190	0.210	4.83	5.33
Q	0.100	0.120	2.54	3.04
R	0.080	0.110	2.04	2.79
S	0.045	0.055	1.15	1.39
T	0.235	0.255	5.97	6.47
U	0.000	0.050	0.00	1.27
V	0.045	---	1.15	---
Z	---	0.080	---	2.04

STYLE 4:

- PIN 1: MAIN TERMINAL 1
2: MAIN TERMINAL 2
3: GATE
4: MAIN TERMINAL 2

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